

# P-Channel 30-V (D-S) MOSFET

#### FEATURES

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

	PRODUCTY SUMMARY				
$V_{\text{DS}}$	R	I <sub>D</sub> (A)			
-30	13	Rdson @-10V	-8.7		
-30	15	Rdson @-4.5V	-8.1		

SOP-8-Single

## Application

- Portable Devices
- Consumer Electronics

#### Mechanical

●Case: SOP-8-Single Package

### **Packing Information**

Package	Packing
SOP-8-Single	2.5K /13" Reel

Maximum Ratings (T <sub>A</sub> =25°C unless otherwise specified)					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V <sub>DS</sub>	-30	V		
Gate-Source Voltage	V <sub>GS</sub>	±20	V		
Continuous Drain Current <sup>1)</sup>	Ι <sub>D</sub>	-15	А		
Maximum Power Dissipation	P <sub>D</sub>	1.1	W		
Pulsed Drain Current <sup>2)</sup>	I <sub>DM</sub>	-60	А		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C		

Typical Thermal Resistance				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient Thermal Resistance	$R_{ extsf{ heta}JA}$	110	°C/W	

Note:

- 1. Fused current that based on wire numbers and diameter
- 2. Repetitive Rating: Pulse width limited by the maximum junction temperature
- 3. 1in2 2oz Cu PCB board



<b>Electrical Characteristics</b> ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)							
Characteristics	Symbol	Test Condition	Limits			11	
Characteristics			Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	$B_{VDSS}$	$V_{GS} = 0V, I_D = -250uA$	-30			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=-250$ uA	-1.00	-1.50	-3.00	V	
Drain-Source On-State Resistance	D	V <sub>GS</sub> =-10.0V, I <sub>D</sub> =-8.7A	-	9	13	mΩ	
	$R_{DS(on)}$	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-8.1A	-	12	15	mΩ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =-30V, $V_{G}$ S=0V			1.0	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V			±100	nA	
		Dynamic <sup>3)</sup>					
Total Gate Charge	$Q_g$		-	26	-	nC	
Gate-Source Charge	$Q_{gs}$	Q <sub>gs</sub> V <sub>DS</sub> =-15V, I <sub>D</sub> =-10A, V <sub>GS</sub> =-4.5V		8.7	-	nC	
Gate-Drain Charge	$Q_{gd}$		-	8.6	-	nC	
Input Capacitance	C <sub>iss</sub>		-	3168	-	pF	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	393	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	258	-	pF	
	-			-			
		Switching					
Turn-On Delay Time	t <sub>d(on)</sub>	<u>·</u>		11	-	ns	
Turn-On Rise Time	t <sub>r</sub>			14	-	ns	
Turn-Off Delay Time	$t_{d(off)}$	V <sub>GS</sub> =-10V,R <sub>G</sub> =6 ଯ	-	102	-	ns	
Turn-Off Fall Time	t <sub>f</sub>		-	47	-	ns	
	Dra	ain-Source Diode			1		
Maximum Continuous Drain-Source	۱ <sub>s</sub>	-	-	-	-12	А	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1.0A, V <sub>GS</sub> =0V	-	-	-1.2	V	

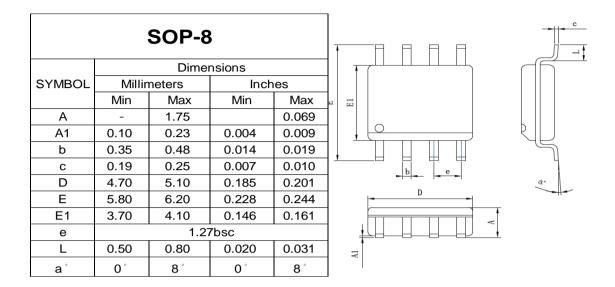
NOTES :

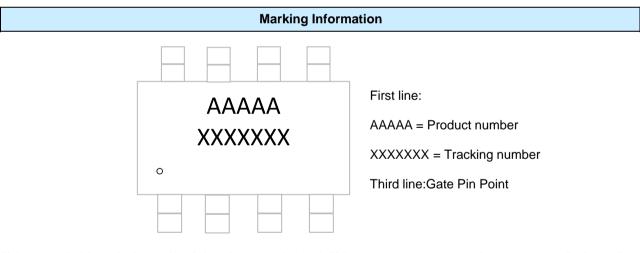
1. Pulse width<300us, Duty cycle<2%.

Pulse width<300us, Duty cycle<2%.</li>
Essentially independent of operating temperature typical characteristics.
Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
The maximum current rating is package limited.
RQJA is the sum of the junctiontocase and casetoambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch2 with 2oz.square pad of copper.
Guaranteed by design. not subject to production testing.



Package Outline Dimensions (inches and millimeters)





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